a' Sub B'

1. (Amended) A die seal structure for a semiconductor die having a substrate comprising:

an elongate region electrically isolated from the remainder of the substrate extending around a major portion of the periphery of the substrate and having a gap between ends of the elongate region along a minor portion of the periphery; and

a conductive seal ring extending around the entire periphery of the die in direct contact with the die throughout said elongate region in direct contact with and said gap to provide a limited electrical connection between the ring and the substrate at said gap.

Please cancel 9-13.

a² Sub B²

14. (Amended) A die seal structure for a semiconductor die having a substrate of a first conductivity type, comprising:

an elongate well region of a second conductivity type opposite from the first conductivity type extending around a major portion of the periphery of the substrate and having a gap between the ends of the elongate region along a minor portion of the periphery; and

a conductive seal ring extending around the entire periphery of the die in direct contact with the die throughout said elongate well region and in said gap to provide a limited electrical connection between the ring and the substrate of said first conductivity type at said gap.

a³ Sub B³

18. (Amended) A semiconductor device comprising:

a. a die including a substrate;

b. a die seal structure on the substrate, the structure comprising:

an elongate region electrically isolated from the remainder of the substrate extending around a major portion of the periphery of the substrate and having a gap between ends of the elongate region along a minor portion of the periphery; and